

# OPAx171-Q1 36-V, Single-Supply, General-Purpose Operational Amplifier

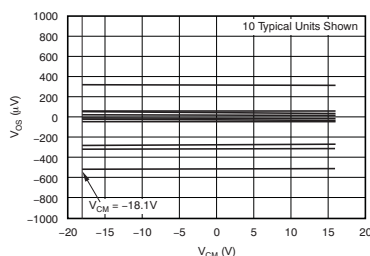
## 1 Features

- Qualified for Automotive Applications
- AEC-Q100 Test Guidance With the Following:
  - Device Temperature Grade 1:  $-40^{\circ}\text{C}$  to  $125^{\circ}\text{C}$  Ambient Operating Temperature Range
  - Device HBM ESD Classification Level H2
  - Device CDM ESD Classification Level C3A (OPA171-Q1) and C6 (OPA2171-Q1, OPA4171-Q1)
- Supply Range: 2.7 to 36 V,  $\pm 1.35$  to  $\pm 18$  V
- Low Noise:  $14\text{ nV}/\sqrt{\text{Hz}}$
- Low Offset Drift:  $\pm 0.3\text{ }\mu\text{V}/^{\circ}\text{C}$  (typ)
- RFI Filtered Inputs
- Input Range Includes the Negative Supply
- Input Range Operates to Positive Supply
- Rail-to-Rail Output
- Gain Bandwidth: 3 MHz
- Low Quiescent Current: 475  $\mu\text{A}$  per Amplifier
- High Common-Mode Rejection: 120 dB (typ)
- Low Input Bias Current: 8 pA
- Industry-Standard Package:
  - 5-Pin Small-Outline Transistor [SOT (SOT-23) - DBV] Package

## 2 Applications

- Tracking Amplifier in Power Modules
- Merchant Power Supplies
- Transducer Amplifiers
- Bridge Amplifiers
- Temperature Measurements
- Strain Gauge Amplifiers
- Precision Integrators
- Battery-Powered Instruments
- Test Equipment

### Offset Voltage vs Common-mode Voltage



## 3 Description

The OPA171-Q1 family of devices is a 36-V, single-supply, low-noise operational amplifier (op amp) with the ability to operate on supplies ranging from 2.7 V ( $\pm 1.35$  V) to 36 V ( $\pm 18$  V). This device is available in micro-packages and offers low offset, drift, and bandwidth with low quiescent current. The single, dual, and quad versions all have identical specifications for maximum design flexibility.

Unlike most op amps, which are specified at only one supply voltage, the OPAx171-Q1 family of devices is specified from 2.7 to 36 V. Input signals beyond the supply rails do not cause phase reversal. The OPAx171-Q1 family of devices is stable with capacitive loads up to 300 pF. The input can operate 100 mV below the negative rail and within 2 V of the top rail during normal operation. The device can operate with full rail-to-rail input 100 mV beyond the top rail, but with reduced performance within 2 V of the top rail.

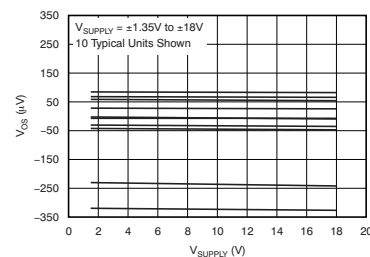
The OPAx171-Q1 op amp is specified from  $-40^{\circ}\text{C}$  to  $125^{\circ}\text{C}$ .

### Device Information<sup>(1)</sup>

PART NUMBER	PACKAGE	BODY SIZE (NOM)
OPA171-Q1	SOT (5)	2.90 mm x 1.60 mm
OPA2171-Q1	SOIC (8)	4.90 mm x 3.91 mm
OPA4171-Q1	SOIC (14)	8.65 mm x 3.91 mm
	TSSOP (14)	5.00 mm x 4.40 mm

(1) For all available packages, see the orderable addendum at the end of the datasheet.

### Offset Voltage vs Power Supply



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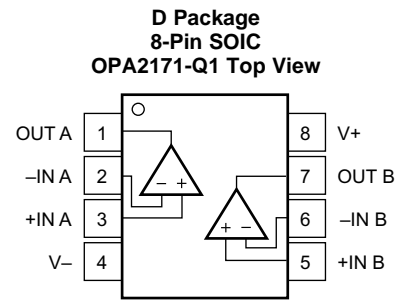
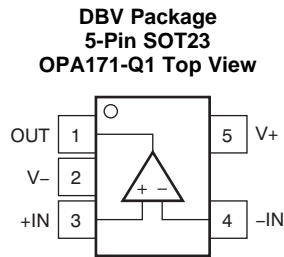
## 4 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

<b>Changes from Revision A (September 2012) to Revision B</b>	<b>Page</b>
• Added the <i>Handling Ratings</i> table, <i>Feature Description</i> section, <i>Device Functional Modes</i> section, <i>Application and Implementation</i> section, <i>Power Supply Recommendations</i> section, <i>Layout</i> section, <i>Device and Documentation Support</i> section, and <i>Mechanical, Packaging, and Orderable Information</i> section .....	<b>1</b>
• Added the OPA2171-Q1 and OPA4171-Q1 devices to the data sheet .....	<b>1</b>

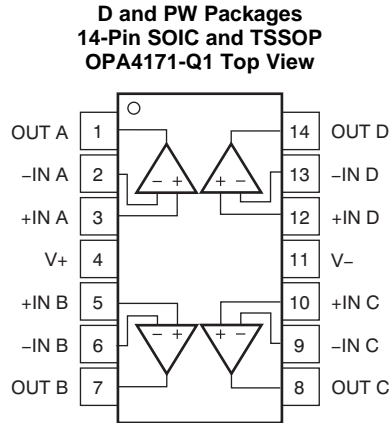
<b>Changes from Original (June, 2011) to Revision A</b>	<b>Page</b>
• Added second bullet to Features: AEC-Q100 Test Guidance With the Following Results: –Device Temperature Grade1: -40°C to 125°C Ambient Operating Temperature Range –Device HBM ESD Classification Level H2 –Device CDM ESD Classification Level C3A .....	<b>1</b>
• Added classification levels to ESD ratings in Absolute Maximum Ratings table. ....	<b>4</b>
• Added row to Absolute Maximum Ratings table: Latch-up per JESD78D with Class 1 value. ....	<b>4</b>

## 5 Pin Configuration and Functions



**Pin Functions — DBV (5) and D (8) Packages**

NAME	PIN		I/O	DESCRIPTION
	OPA171-Q1 DBV (5)	OPA2171-Q1 D (8)		
+IN	3	—	I	Noninverting input
+IN A	—	3	I	Noninverting input, channel A
+IN B	—	5	I	Noninverting input, channel B
-IN	4	—	I	Inverting input
-IN A	—	2	I	Inverting input, channel A
-IN B	—	6	I	Inverting input, channel B
OUT	1	—	O	Output
OUT A	—	1	O	Output, channel A
OUT B	—	7	O	Output, channel B
V+	5	7	—	Positive (highest) power supply
V-	2	4	—	Negative (lowest) power supply



**Pin Functions — D (14) and PW (14) Packages**

PIN		I/O	DESCRIPTION
NAME	D (14), PW (14)		
+IN A	3	I	Noninverting input, channel A
+IN B	5	I	Noninverting input, channel B
+IN C	10	I	Noninverting input, channel C
+IN D	12	I	Noninverting input, channel D
-IN A	2	I	Inverting input, channel A
-IN B	6	I	Inverting input, channel B
-IN C	9	I	Inverting input, channel C
-IN D	13	I	Inverting input, channel D
OUT A	1	O	Output, channel A
OUT B	7	O	Output, channel B
OUT C	8	O	Output, channel C
OUT D	14	O	Output, channel D
V+	4	—	Positive (highest) power supply
V-	11	—	Negative (lowest) power supply

## 6 Specifications

### 6.1 Absolute Maximum Ratings

Over operating free-air temperature range, unless otherwise noted.<sup>(1)</sup>

		MIN	MAX	UNIT
Supply voltage			40	V
Signal input terminals	Voltage	(V-) - 0.5	(V+) + 0.5	V
	Current		±10	mA
Output short circuit <sup>(2)</sup>		Continuous		
Operating temperature		-55	150	°C
Junction temperature			150	°C
Latch-up per JESD78D		Class 1		
Storage temperature, T <sub>stg</sub>		-65	150	°C

(1) Stresses above these ratings may cause permanent damage. Exposure to absolute maximum conditions for extended periods may degrade device reliability. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those specified is not implied.

(2) Short-circuit to ground, one amplifier per package.

## 6.2 ESD Ratings

			VALUE	UNIT
<b>OPA171-Q1 IN DBV PACKAGE</b>				
V <sub>(ESD)</sub>	Electrostatic discharge	Human body model (HBM), per AEC Q100-002 <sup>(1)</sup>	±4000	V
		Charged device model (CDM), per AEC Q100-011	±500	
<b>OPA2171-Q1 IN D PACKAGE AND OPA4171-Q1 IN D AND PW PACKAGES</b>				
V <sub>(ESD)</sub>	Electrostatic discharge	Human body model (HBM), per AEC Q100-002 <sup>(1)</sup>	±2000	V
		Charged device model (CDM), per AEC Q100-011	±1000	

(1) AEC Q100-002 indicates HBM stressing is done in accordance with the ANSI/ESDA/JEDEC JS-001 specification.

## 6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

	MIN	NOM	MAX	UNIT
Supply voltage (V <sub>+</sub> – V <sub>–</sub> )	4.5 (±2.25)		36 (±18)	V
Specified temperature	–40		125	°C

## 6.4 Thermal Information — OPA171-Q1 and OPA2171-Q1

THERMAL METRIC <sup>(1)</sup>		OPA171-Q1	OPA2171-Q1	UNIT
		DBV 5 PINS	D 8 PINS	
R <sub>θJA</sub>	Junction-to-ambient thermal resistance	277.3	116.1	°C/W
R <sub>θJC(top)</sub>	Junction-to-case(top) thermal resistance	193.3	69.8	
R <sub>θJB</sub>	Junction-to-board thermal resistance	121.2	56.6	
Ψ <sub>JT</sub>	Junction-to-top characterization parameter	51.8	22.5	
Ψ <sub>JB</sub>	Junction-to-board characterization parameter	109.5	56.1	

(1) For more information about traditional and new thermal metrics, see the *IC Package Thermal Metrics* application report, [SPRA953](#).

## 6.5 Thermal Information — OPA4171-Q1

THERMAL METRIC <sup>(1)</sup>		OPA4171-Q1		UNIT
		D 14 PINS	PW 14 PINS	
R <sub>θJA</sub>	Junction-to-ambient thermal resistance	93.2	106.9	°C/W
R <sub>θJC(top)</sub>	Junction-to-case(top) thermal resistance	51.8	24.4	
R <sub>θJB</sub>	Junction-to-board thermal resistance	49.4	59.3	
Ψ <sub>JT</sub>	Junction-to-top characterization parameter	13.5	0.6	
Ψ <sub>JB</sub>	Junction-to-board characterization parameter	42.2	54.3	

(1) For more information about traditional and new thermal metrics, see the *IC Package Thermal Metrics* application report, [SPRA953](#).

## 6.6 Electrical Characteristics

At T<sub>A</sub> = 25°C, V<sub>S</sub> = 2.7 to 36 V, V<sub>CM</sub> = V<sub>OUT</sub> = V<sub>S</sub> / 2, and R<sub>LOAD</sub> = 10 kΩ connected to V<sub>S</sub> / 2, unless otherwise noted. The specified temperature range is T<sub>A</sub> = –40°C to 125°C.

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
<b>OFFSET VOLTAGE</b>					
V <sub>OS</sub>	Input offset voltage		0.25	±1.8	mV
	Input offset voltage over temperature		0.3	±2	mV
dV <sub>OS</sub> /dT	Input offset voltage drift (over temperature)		0.3	±2 <sup>(1)</sup>	μV/°C
PSRR	Input offset voltage over temperature vs power supply	V <sub>S</sub> = 4 to 36 V	1	±3	μV/V
	Channel separation, DC		5		μV/V

(1) Not production tested.

## Electrical Characteristics (continued)

At  $T_A = 25^\circ\text{C}$ ,  $V_S = 2.7$  to  $36\text{ V}$ ,  $V_{CM} = V_{OUT} = V_S / 2$ , and  $R_{LOAD} = 10\text{ k}\Omega$  connected to  $V_S / 2$ , unless otherwise noted. The specified temperature range is  $T_A = -40^\circ\text{C}$  to  $125^\circ\text{C}$ .

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
<b>INPUT BIAS CURRENT</b>						
$I_B$	Input bias current			$\pm 8$	$\pm 15$	$\mu\text{A}$
	Input bias current over temperature				$\pm 3.5$	$\text{nA}$
$I_{OS}$	Input offset current			$\pm 4$		$\mu\text{A}$
	Input offset current over temperature				$\pm 3.5$	$\text{nA}$
<b>NOISE</b>						
	Input voltage noise	$f = 0.1\text{ Hz to }10\text{ Hz}$		3		$\mu\text{V}_{PP}$
$e_n$	Input voltage noise density	$f = 100\text{ Hz}$		25		$\text{nV}/\sqrt{\text{Hz}}$
		$f = 1\text{ kHz}$		14		$\text{nV}/\sqrt{\text{Hz}}$
<b>INPUT VOLTAGE</b>						
$V_{CM}$	Common-mode voltage range <sup>(2)</sup>		$(V-) - 0.1$		$(V+) - 2$	$\text{V}$
CMRR	Common-mode rejection ratio (over temperature)	$V_S = \pm 2\text{ V}, (V-) - 0.1\text{ V} < V_{CM} < (V+) - 2\text{ V}$	90	104		$\text{dB}$
		$V_S = \pm 18\text{ V}, (V-) - 0.1\text{ V} < V_{CM} < (V+) - 2\text{ V}$	104	120		$\text{dB}$
<b>INPUT IMPEDANCE</b>						
	Differential			$100 \parallel 3$		$\text{M}\Omega \parallel \text{pF}$
	Common-mode			$6 \parallel 3$		$10^{12}\Omega \parallel \text{pF}$
<b>OPEN-LOOP GAIN</b>						
$A_{OL}$	Open-loop voltage gain (over temperature)	$V_S = +4\text{V to }+36\text{V}, (V-) + 0.35\text{V} < V_O < (V+) - 0.35\text{V}$	110	130		$\text{dB}$
<b>FREQUENCY RESPONSE</b>						
GBP	Gain bandwidth product			3.0		$\text{MHz}$
SR	Slew rate	$G = 1$		1.5		$\text{V}/\mu\text{s}$
$t_S$	Settling time	To 0.1%, $V_S = \pm 18\text{ V}, G = 1, 10\text{-V step}$		6		$\mu\text{s}$
		To 0.01% (12 bit), $V_S = \pm 18\text{ V}, G = 1, 10\text{-V step}$		10		$\mu\text{s}$
	Overload recovery time	$V_{\text{IN}} \times \text{Gain} > V_S$		2		$\mu\text{s}$
THD+N	Total harmonic distortion + noise	$G = 1, f = 1\text{ kHz}, V_O = 3\text{ V}_{RMS}$		0.0002%		
<b>OUTPUT</b>						
$V_O$	Voltage output swing from rail (over temperature)	$R_L = 10\text{ k}\Omega, A_{OL} \geq 110\text{ dB}$	$(V-) + 0.35$		$(V+) - 0.35$	$\text{V}$
$I_{SC}$	Short-circuit current	Sourcing		25		$\text{mA}$
		Sinking		-35		
$C_{LOAD}$	Capacitive load drive		See the <a href="#">Typical Characteristics</a> section			$\text{pF}$
$R_O$	Open-loop output resistance	$f = 1\text{ MHz}, I_O = 0\text{ A}$		150		$\Omega$
<b>POWER SUPPLY</b>						
$V_S$	Specified voltage range		2.7		36	$\text{V}$
$I_Q$	Quiescent current per amplifier	$I_O = 0\text{ A}$		475	595	$\mu\text{A}$
	Quiescent current per amplifier (over temperature)	$I_O = 0\text{ A}$			650	$\mu\text{A}$
<b>TEMPERATURE</b>						
	Specified range		-40		125	$^\circ\text{C}$
	Operating range		-55		150	$^\circ\text{C}$

(2) The input range can be extended beyond  $(V+) - 2\text{ V}$  up to  $V+$ . See the and [Detailed Description](#) sections for additional information.

## 6.7 Typical Characteristics

$V_S = \pm 18V$ ,  $V_{CM} = V_S/2$ ,  $R_{LOAD} = 10k\Omega$  connected to  $V_S/2$ , and  $C_L = 100pF$ , unless otherwise noted.

**Table 1. Characteristic Performance Measurements**

DESCRIPTION	FIGURE
Offset Voltage Production Distribution	<a href="#">Figure 1</a>
Offset Voltage Drift Distribution	<a href="#">Figure 2</a>
Offset Voltage vs Temperature	<a href="#">Figure 3</a>
Offset Voltage vs Common-Mode Voltage	<a href="#">Figure 4</a>
Offset Voltage vs Common-Mode Voltage (Upper Stage)	<a href="#">Figure 5</a>
Offset Voltage vs Power Supply	<a href="#">Figure 6</a>
$I_B$ and $I_{OS}$ vs Common-Mode Voltage	<a href="#">Figure 7</a>
Input Bias Current vs Temperature	<a href="#">Figure 8</a>
Output Voltage Swing vs Output Current (Maximum Supply)	<a href="#">Figure 9</a>
CMRR and PSRR vs Frequency (Referred-to Input)	<a href="#">Figure 10</a>
CMRR vs Temperature	<a href="#">Figure 11</a>
PSRR vs Temperature	<a href="#">Figure 12</a>
0.1Hz to 10Hz Noise	<a href="#">Figure 13</a>
Input Voltage Noise Spectral Density vs Frequency	<a href="#">Figure 14</a>
THD+N Ratio vs Frequency	<a href="#">Figure 15</a>
THD+N vs Output Amplitude	<a href="#">Figure 16</a>
Quiescent Current vs Temperature	<a href="#">Figure 17</a>
Quiescent Current vs Supply Voltage	<a href="#">Figure 18</a>
Open-Loop Gain and Phase vs Frequency	<a href="#">Figure 19</a>
Closed-Loop Gain vs Frequency	<a href="#">Figure 20</a>
Open-Loop Gain vs Temperature	<a href="#">Figure 21</a>
Open-Loop Output Impedance vs Frequency	<a href="#">Figure 22</a>
Small-Signal Overshoot vs Capacitive Load (100-mV Output Step)	<a href="#">Figure 23, Figure 24</a>
No Phase Reversal	<a href="#">Figure 25</a>
Positive Overload Recovery	<a href="#">Figure 26</a>
Negative Overload Recovery	<a href="#">Figure 27</a>
Small-Signal Step Response (100 mV)	<a href="#">Figure 28, Figure 29</a>
Large-Signal Step Response	<a href="#">Figure 30, Figure 31</a>
Large-Signal Settling Time (10-V Positive Step)	<a href="#">Figure 32</a>
Large-Signal Settling Time (10-V Negative Step)	<a href="#">Figure 33</a>
Short-Circuit Current vs Temperature	<a href="#">Figure 34</a>
Maximum Output Voltage vs Frequency	<a href="#">Figure 35</a>
Channel Separation vs Frequency	<a href="#">Figure 36</a>

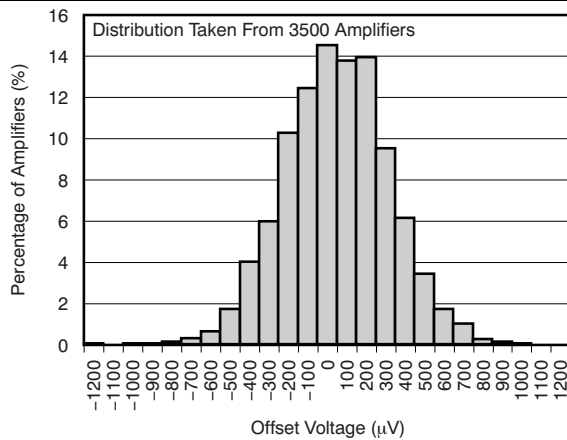


Figure 1. Offset Voltage Production Distribution

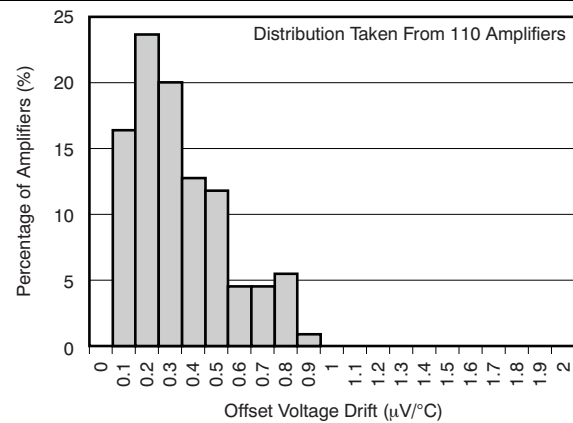


Figure 2. Offset Voltage Drift Distribution

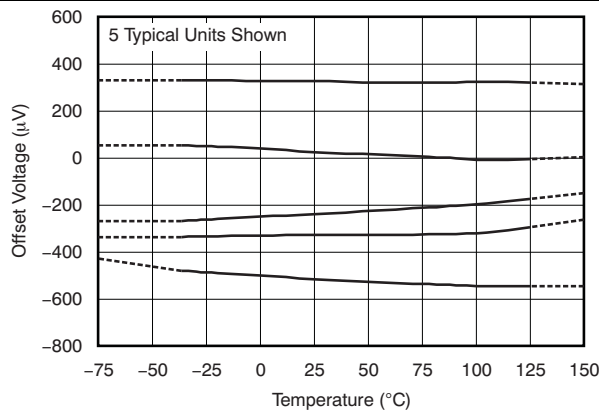


Figure 3. Offset Voltage vs Temperature

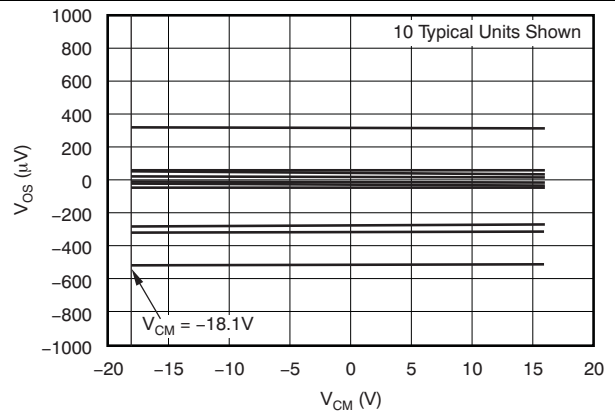


Figure 4. Offset Voltage vs Common-mode Voltage

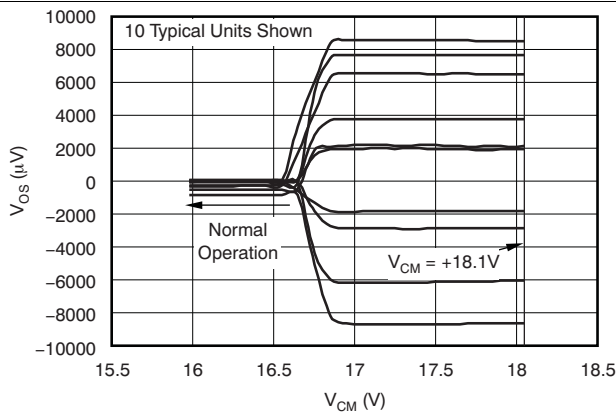


Figure 5. Offset Voltage vs Common-mode Voltage (Upper Stage)

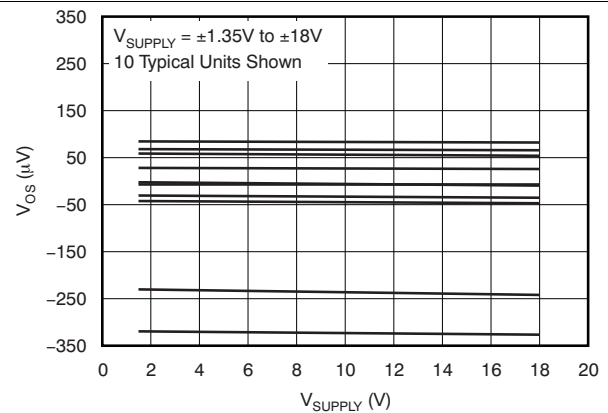


Figure 6. Offset Voltage vs Power Supply

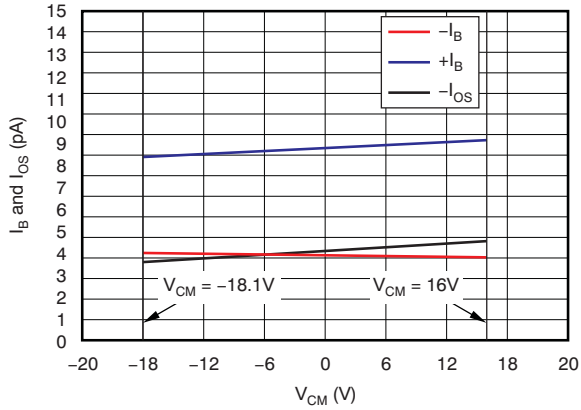


Figure 7.  $I_B$  and  $I_{OS}$  vs Common-Mode Voltage

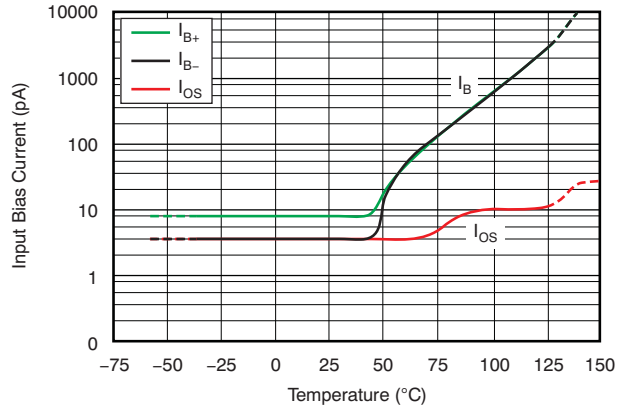


Figure 8. Input Bias Current vs Temperature

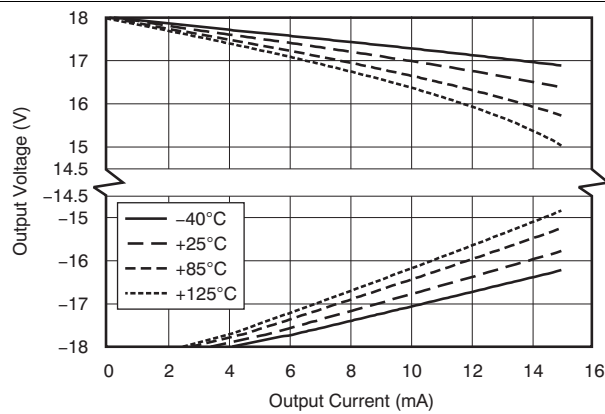


Figure 9. Output Voltage Swing vs Output Current (Maximum Supply)

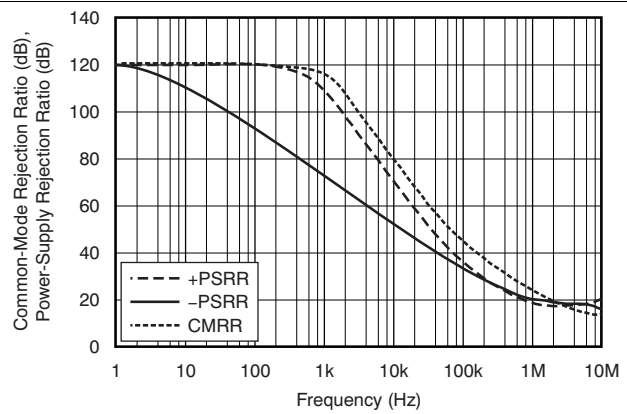


Figure 10. CMRR and PSRR vs Frequency (Referred-to-Input)

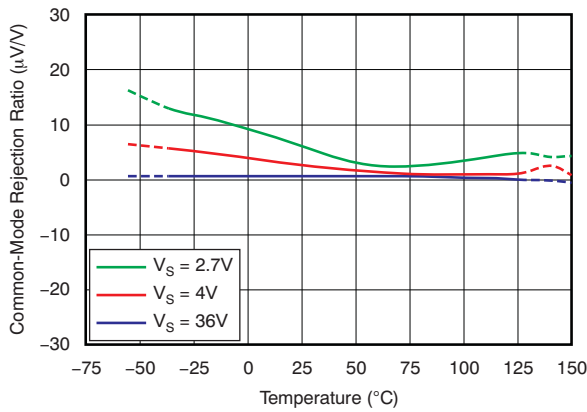


Figure 11. CMRR vs Temperature

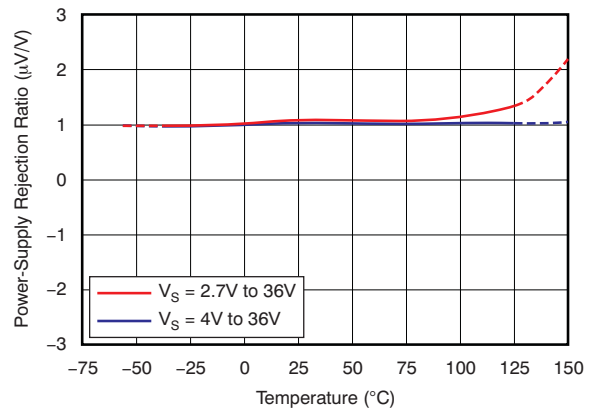


Figure 12. PSRR vs Temperature

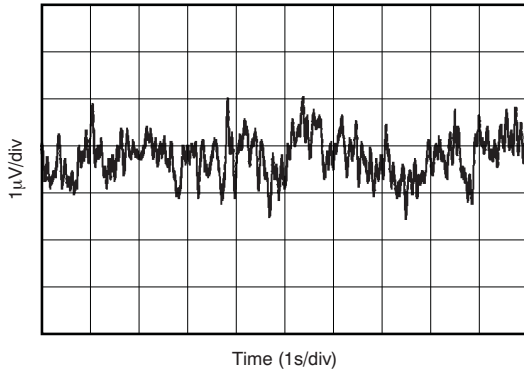


Figure 13. 0.1- to 10-Hz Noise

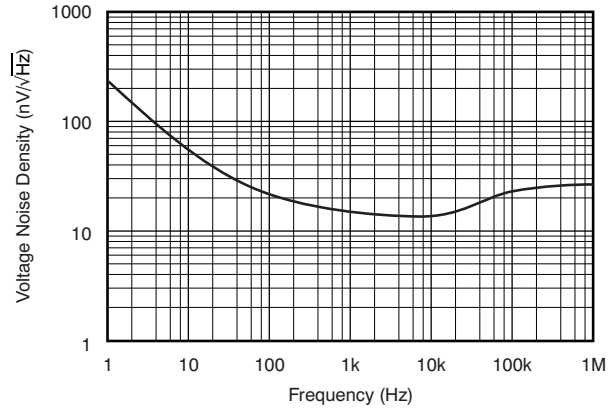


Figure 14. Input Voltage Noise Spectral Density vs Frequency

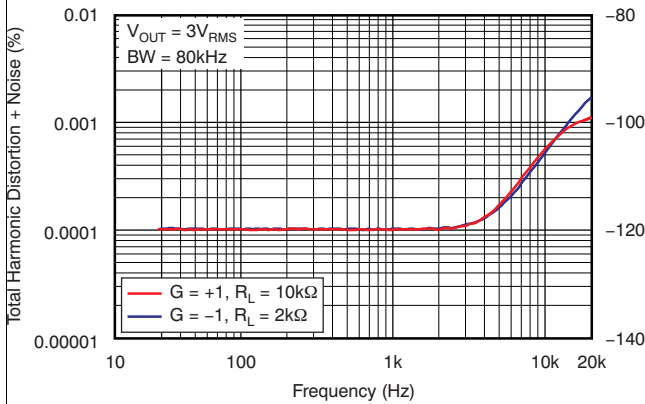


Figure 15. THD+N Ratio vs Frequency

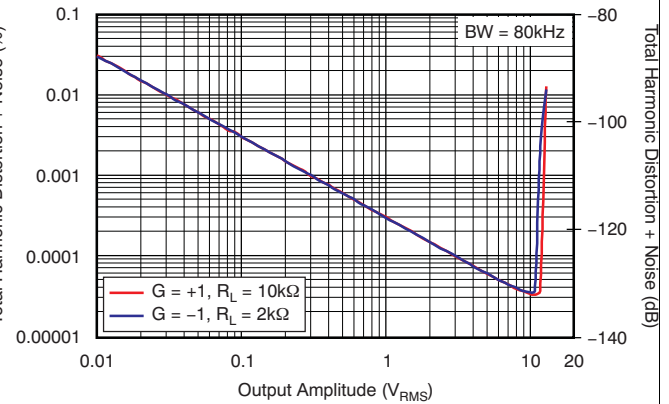


Figure 16. THD+N vs Output Amplitude

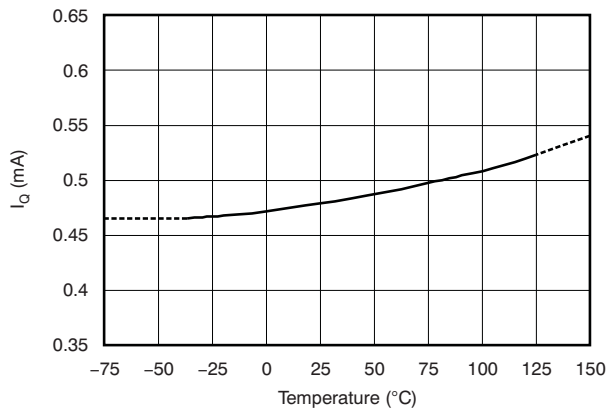


Figure 17. Quiescent Current vs Temperature

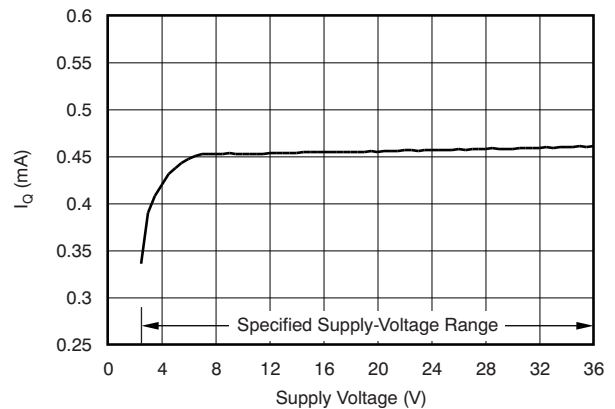


Figure 18. Quiescent Current vs Supply Voltage

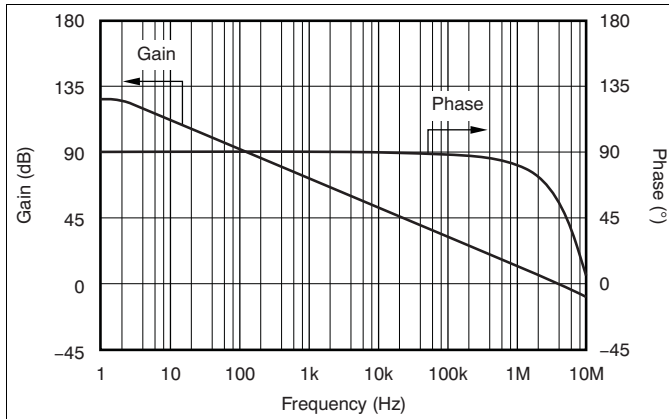


Figure 19. Open-Loop Gain and Phase vs Frequency

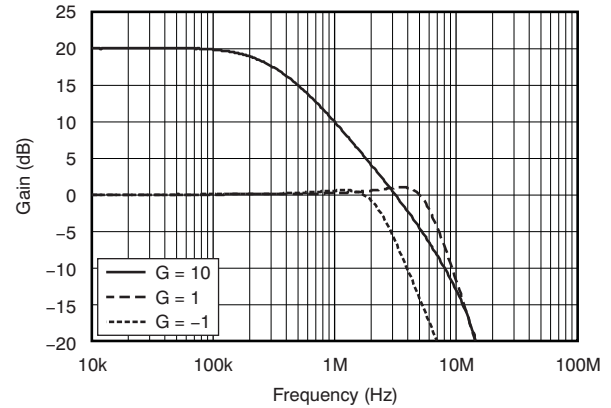


Figure 20. Closed-Loop Gain vs Frequency

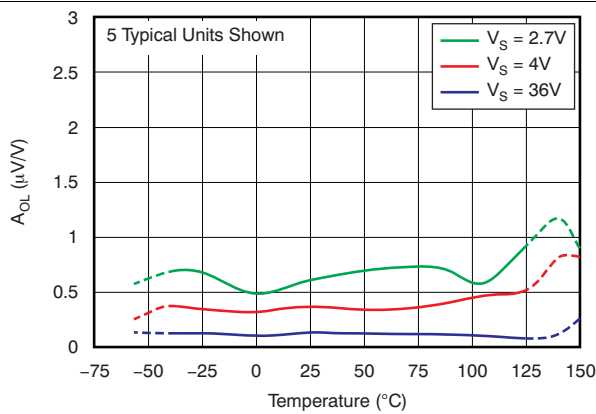


Figure 21. Open-Loop Gain vs Temperature

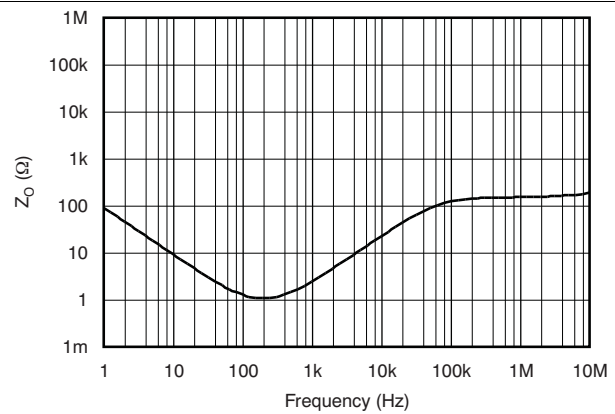


Figure 22. Open-Loop Output Impedance vs Frequency

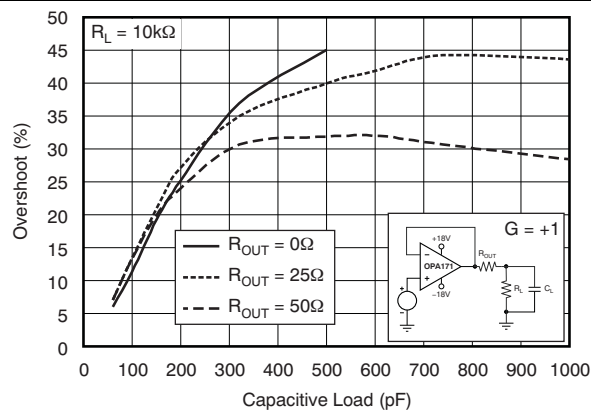


Figure 23. Small-Signal Overshoot vs Capacitive Load (100-mV Output Step)

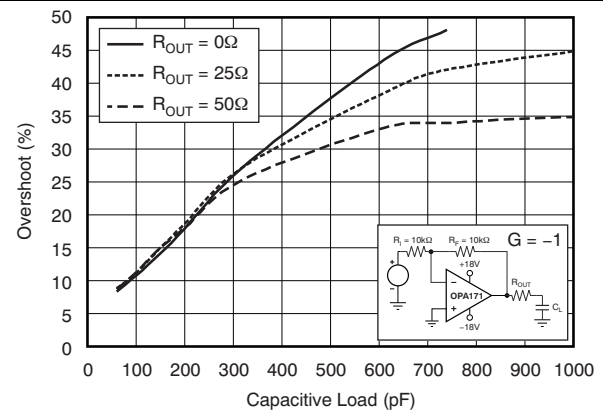


Figure 24. Small-Signal Overshoot vs Capacitive Load (100-mV Output Step)

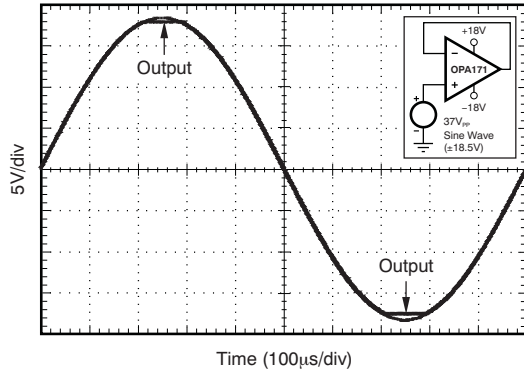


Figure 25. No Phase Reversal

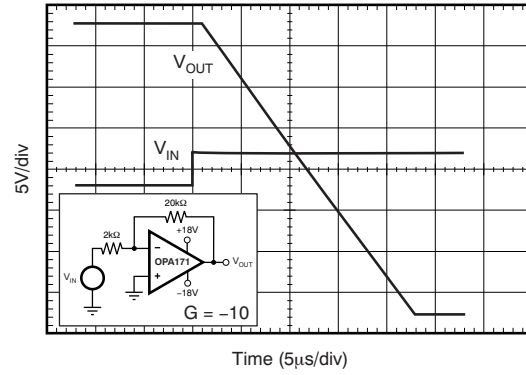


Figure 26. Positive Overload Recovery

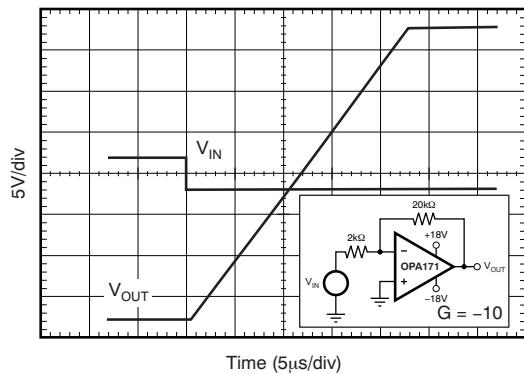


Figure 27. Negative Overload Recovery

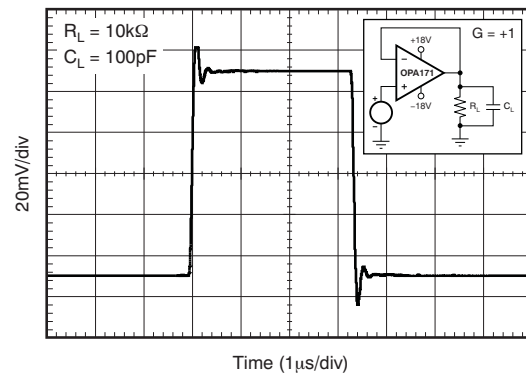


Figure 28. Small-Signal Step Response (100 mV)

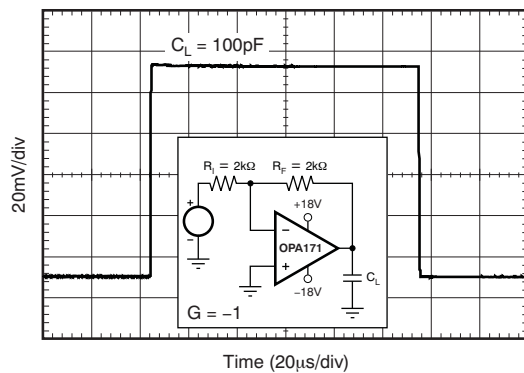


Figure 29. Small-Signal Step Response (100 mV)

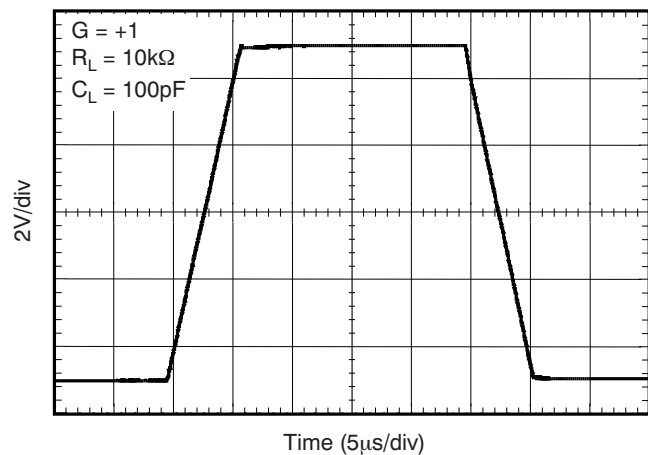


Figure 30. Large-Signal Step Response

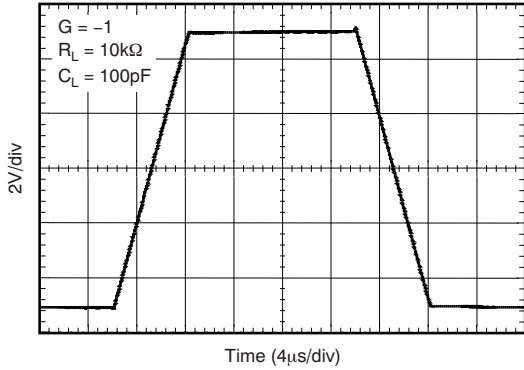


Figure 31. Large-Signal Step Response

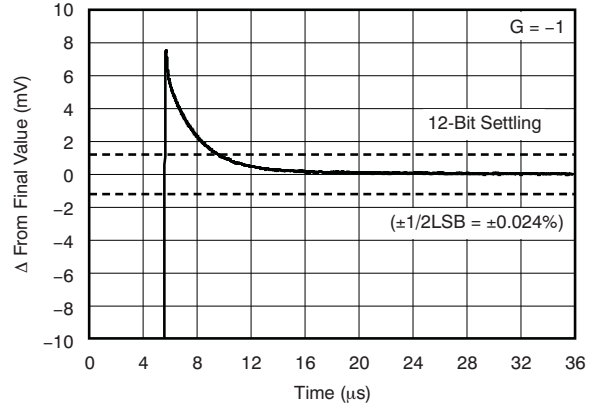


Figure 32. Large-Signal Settling Time (10-V Positive Step)

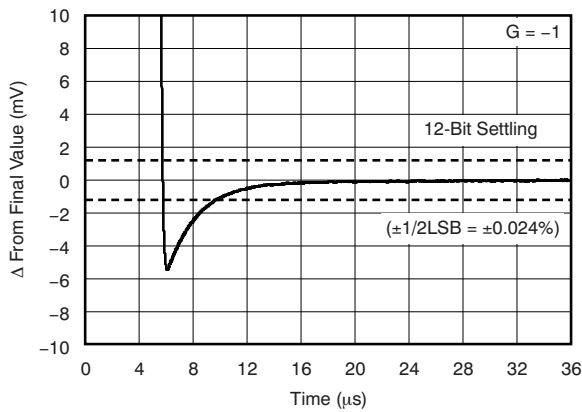


Figure 33. Large-Signal Settling Time (10-V Negative Step)

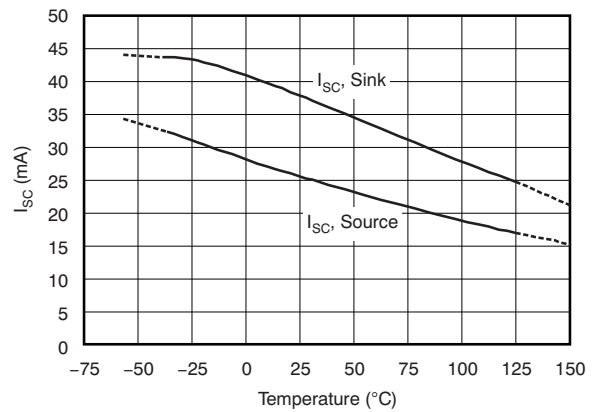


Figure 34. Short-Circuit Current vs Temperature

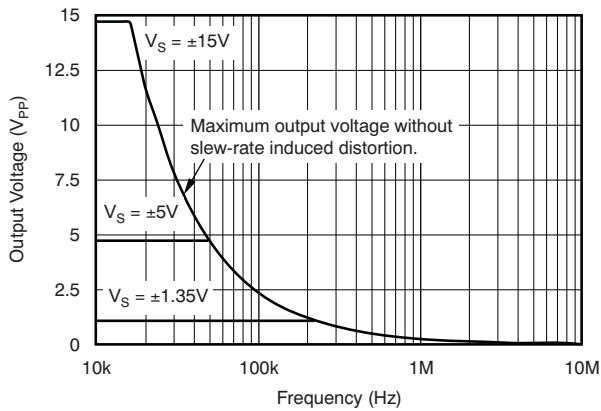


Figure 35. Maximum Output Voltage vs Frequency

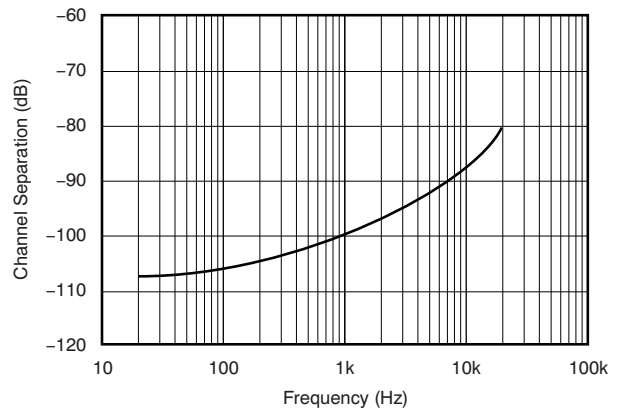


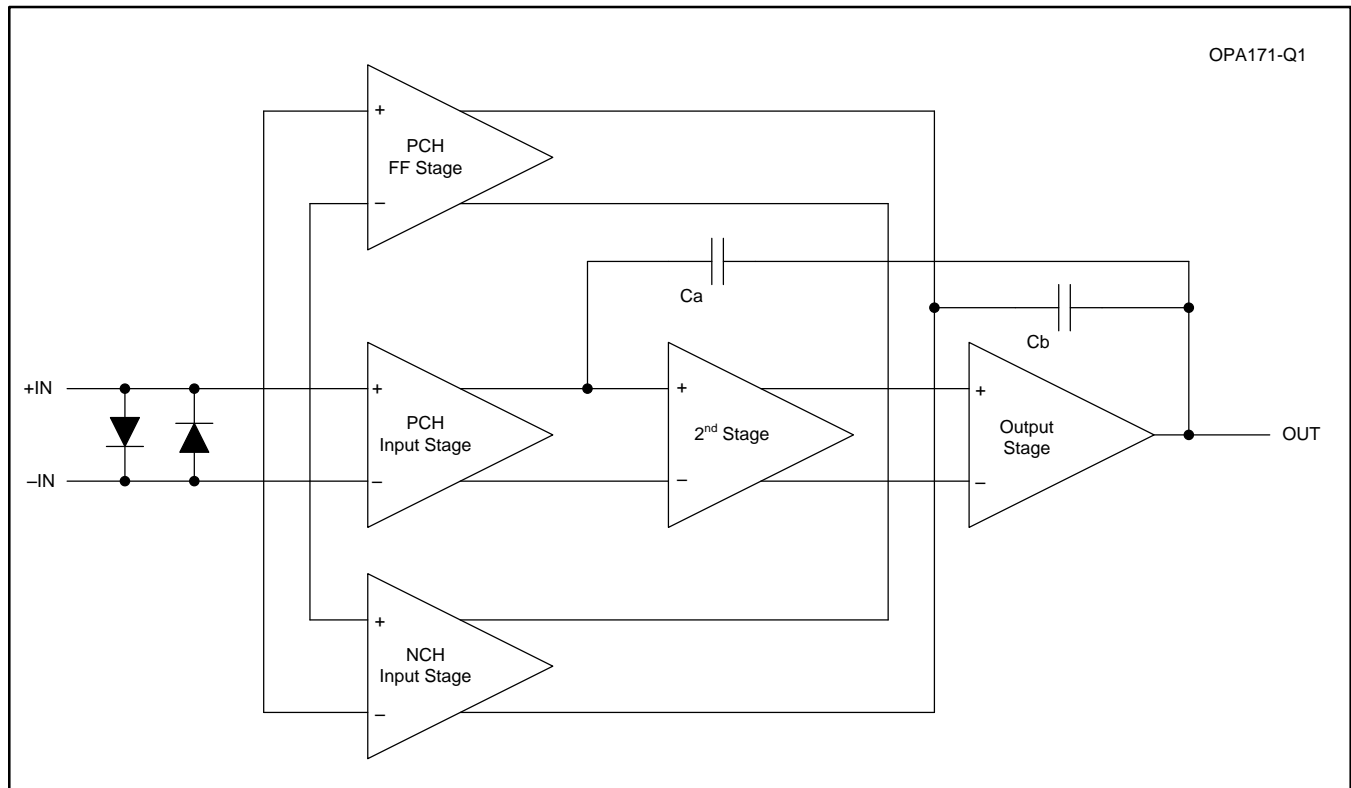
Figure 36. Channel Separation vs Frequency

## 7 Detailed Description

### 7.1 Overview

The OPAx171-Q1 family of operational amplifiers provide high overall performance, making them ideal for many general-purpose applications. The excellent offset drift of only 1.5  $\mu\text{V}/^\circ\text{C}$  (maximum) provides excellent stability over the entire temperature range. In addition, the device offers very good overall performance with high CMRR, PSRR, AOL, and superior THD.

### 7.2 Functional Block Diagram



### 7.3 Feature Description

#### 7.3.1 Operating Characteristics

The OPAx171-Q1 family of devices is specified for operation from 2.7 to 36 V ( $\pm 1.35$  to  $\pm 18$  V). Many of the specifications apply from  $-40^\circ\text{C}$  to  $125^\circ\text{C}$ . Parameters that can exhibit significant variance with regard to operating voltage or temperature are shown in the section.

#### 7.3.2 Phase-Reversal Protection

The OPAx171-Q1 family of devices has an internal phase-reversal protection. Many op amps exhibit a phase reversal when the input is driven beyond its linear common-mode range. This condition is most often encountered in noninverting circuits when the input is driven beyond the specified common-mode voltage range, causing the output to reverse into the opposite rail. The input of the OPAx171 family of devices prevents phase reversal with excessive common-mode voltage. Instead, the output limits into the appropriate rail. [Figure 37](#) shows this performance.

Feature Description (continued)

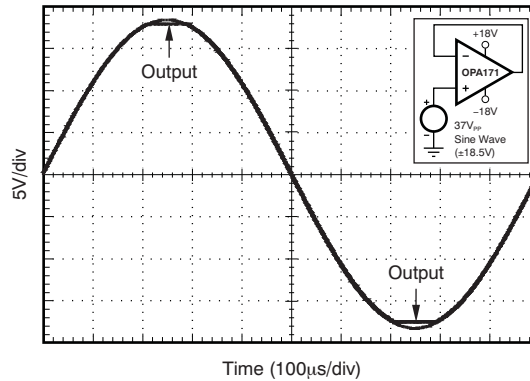


Figure 37. No Phase Reversal

7.3.3 Capacitive Load and Stability

The dynamic characteristics of the OPAx171-Q1 family of devices have been optimized for commonly encountered operating conditions. The combination of low closed-loop gain and high capacitive loads decreases the phase margin of the amplifier and can lead to gain peaking or oscillations. As a result, heavier capacitive loads must be isolated from the output. The simplest way to achieve this isolation is to add a small resistor (for example,  $R_{OUT}$  equal to 50  $\Omega$ ) in series with the output. Figure 38 and Figure 39 show small-signal overshoot versus capacitive load for several values of  $R_{OUT}$ . Also, for details of analysis techniques and application circuits, refer to the *Applications Bulletin AB-028 (SBOA015)*, available for download from [TI.com](http://TI.com).

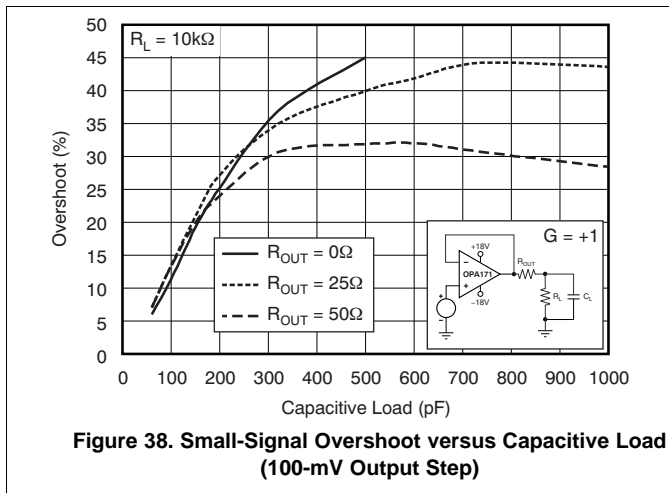


Figure 38. Small-Signal Overshoot versus Capacitive Load (100-mV Output Step)

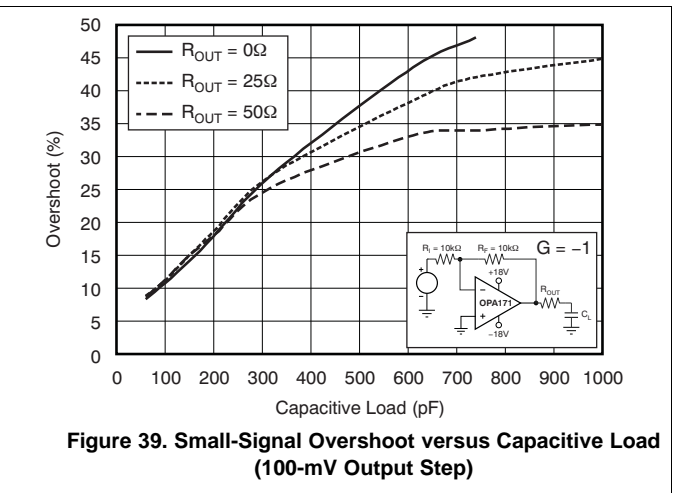


Figure 39. Small-Signal Overshoot versus Capacitive Load (100-mV Output Step)

## 7.4 Device Functional Modes

### 7.4.1 Common-Mode Voltage Range

The input common-mode voltage range of the OPAx171 family of devices extends 100 mV below the negative rail and within 2 V of the top rail for normal operation.

This device can operate with full rail-to-rail input 100 mV beyond the top rail, but with reduced performance within 2 V of the top rail. The typical performance in this range is summarized in [Table 2](#).

**Table 2. Typical Performance Range**

PARAMETER	MIN	TYP	MAX	UNIT
<b>Input Common-Mode Voltage</b>	<b>(V+) – 2</b>		<b>(V+) + 0.1</b>	<b>V</b>
Offset voltage		7		mV
<b>vs Temperature</b>		<b>12</b>		<b>μV/°C</b>
Common-mode rejection		65		dB
Open-loop gain		60		dB
GBW		0.7		MHz
Slew rate		0.7		V/μs
Noise at f = 1kHz		30		nV/√Hz

## 8 Application and Implementation

### NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

### 8.1 Application Information

The OPAx171-Q1 operational amplifier provides high overall performance, making it ideal for many general-purpose applications. The excellent offset drift of only  $2 \mu\text{V}/^\circ\text{C}$  provides excellent stability over the entire temperature range. In addition, the device offers very-good overall performance with high CMRR, PSRR, and  $A_{OL}$ . As with all amplifiers, applications with noisy or high-impedance power supplies require decoupling capacitors close to the device pins. In most cases,  $0.1\text{-}\mu\text{F}$  capacitors are adequate.

#### 8.1.1 Electrical Overstress

Designers often ask questions about the capability of an op amp to withstand electrical overstress. These questions tend to focus on the device inputs, but may involve the supply voltage pins or even the output pin. Each of these different pin functions have electrical stress limits determined by the voltage breakdown characteristics of the particular semiconductor fabrication process and specific circuits connected to the pin. Additionally, internal electrostatic discharge (ESD) protection is built into these circuits to protect them from accidental ESD events both before and during product assembly.

These ESD protection diodes also provide in-circuit, input overdrive protection, as long as the current is limited to 10 mA as stated in the *Absolute Maximum Ratings* table. Figure 40 shows how a series input resistor can be added to the driven input to limit the input current. The added resistor contributes thermal noise at the amplifier input and its value should be kept to a minimum in noise-sensitive applications.

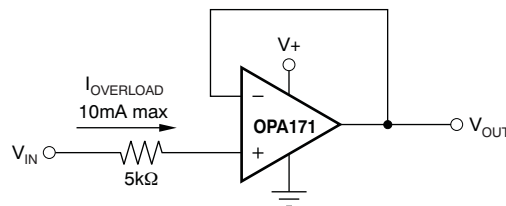


Figure 40. Input Current Protection

An ESD event produces a short duration, high-voltage pulse that is transformed into a short duration, high-current pulse as it discharges through a semiconductor device. The ESD protection circuits are designed to provide a current path around the operational amplifier core to prevent it from being damaged. The energy absorbed by the protection circuitry is then dissipated as heat.

When the operational amplifier connects into a circuit, the ESD protection components are intended to remain inactive and not become involved in the application circuit operation. However, circumstances may arise where an applied voltage exceeds the operating voltage range of a given pin. Should this condition occur, there is a risk that some of the internal ESD protection circuits may be biased on, and conduct current. Any such current flow occurs through ESD cells and rarely involves the absorption device.

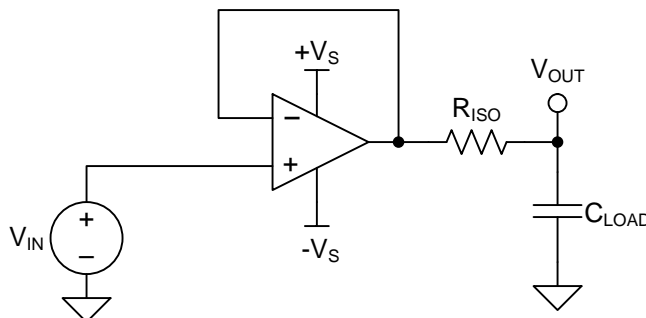
If the ability of the supply to absorb this current is uncertain, external zener diodes may be added to the supply pins. The zener voltage must be selected such that the diode does not turn on during normal operation.

However, the zener voltage should be low enough so that the zener diode conducts if the supply pin begins to rise above the safe operating supply voltage level.

## 8.2 Typical Application

### 8.2.1 Capacitive Load Drive Solution Using an Isolation Resistor

The OPA171-Q1 device can be used capacitive loads such as cable shields, reference buffers, MOSFET gates, and diodes. The circuit uses an isolation resistor ( $R_{ISO}$ ) to stabilize the output of an op amp.  $R_{ISO}$  modifies the open loop gain of the system to ensure the circuit has sufficient phase margin.



**Figure 41. Unity-Gain Buffer with  $R_{ISO}$  Stability Compensation**

#### 8.2.1.1 Design Requirements

The design requirements are:

- Supply voltage: 30 V ( $\pm 15$  V)
- Capacitive loads: 100 pF, 1000 pF, 0.01  $\mu$ F, 0.1  $\mu$ F, and 1  $\mu$ F
- Phase margin: 45° and 60°

#### 8.2.1.2 Detailed Design Procedure

shows a unity-gain buffer driving a capacitive load. Equation 1 shows the transfer function for the circuit in . Not shown in is the open-loop output resistance of the op amp,  $R_o$ .

$$T(s) = \frac{1 + C_{LOAD} \times R_{ISO} \times s}{1 + (R_o + R_{ISO}) \times C_{LOAD} \times s} \quad (1)$$

The transfer function in Equation 1 has a pole and a zero. The frequency of the pole ( $f_p$ ) is determined by  $(R_o + R_{ISO})$  and  $C_{LOAD}$ . Components  $R_{ISO}$  and  $C_{LOAD}$  determine the frequency of the zero ( $f_z$ ). A stable system is obtained by selecting  $R_{ISO}$  such that the rate of closure (ROC) between the open-loop gain ( $A_{OL}$ ) and  $1/\beta$  is 20 dB/decade. Figure 42 depicts the concept. The  $1/\beta$  curve for a unity-gain buffer is 0 dB.

Typical Application (continued)

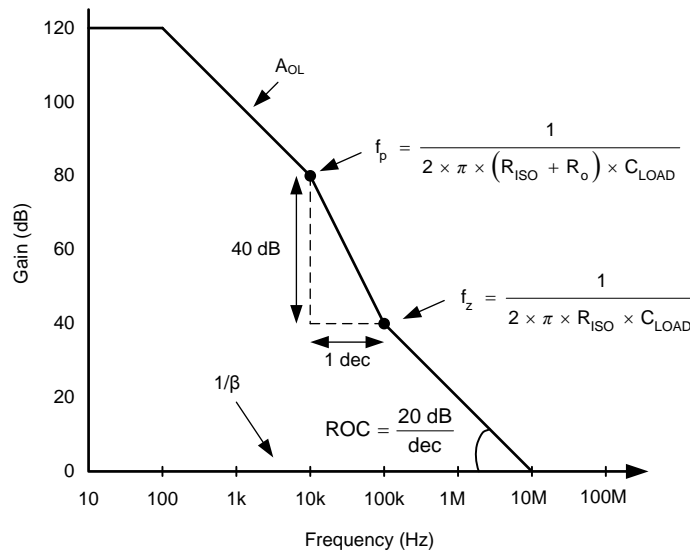


Figure 42. Unity-Gain Amplifier with  $R_{ISO}$  Compensation

ROC stability analysis is typically simulated. The validity of the analysis depends on multiple factors, especially the accurate modeling of  $R_o$ . In addition to simulating the ROC, a robust stability analysis includes a measurement of overshoot percentage and AC gain peaking of the circuit using a function generator, oscilloscope, and gain and phase analyzer. Phase margin is then calculated from these measurements. shows the overshoot percentage and AC gain peaking that correspond to phase margins of 45° and 60°. For more details on this design and other alternative devices that can be used in place of the OPA171, refer to the Precision Design, *Capacitive Load Drive Solution using an Isolation Resistor (TIPD128)*.

Table 3. Phase Margin versus Overshoot and AC Gain Peaking

PHASE MARGIN	OVERSHOOT	AC GAIN PEAKING
45°	23.3%	2.35 dB
60°	8.8%	0.28 dB

8.2.1.3 Application Curves

The OPA171-Q1 device meets the supply voltage requirements of 30 V. The OPA171-Q1 device was tested for various capacitive loads and  $R_{ISO}$  was adjusted to achieve an overshoot corresponding to . shows the test results.

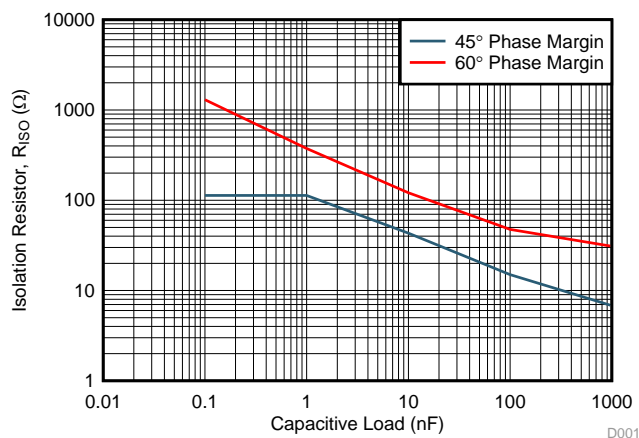


Figure 43.  $R_{ISO}$  vs  $C_{LOAD}$

## 9 Power Supply Recommendations

The OPAx171-Q1 family of devices is specified for operation from 4.5 V to 36 V ( $\pm 2.25$  V to  $\pm 18$  V); many specifications apply from  $-40^{\circ}\text{C}$  to  $125^{\circ}\text{C}$ . Parameters that can exhibit significant variance with regard to operating voltage or temperature are presented in the [Typical Characteristics](#) section.

### CAUTION

Supply voltages larger than 40 V can permanently damage the device; see the [Absolute Maximum Ratings](#) table.

Place 0.1- $\mu\text{F}$  bypass capacitors close to the power-supply pins to reduce errors coupling in from noisy or high-impedance power supplies. For detailed information on bypass capacitor placement, see the [Layout](#) section.

## 10 Layout

### 10.1 Layout Guidelines

For best operational performance of the device, use good printed circuit board (PCB) layout practices, including:

- Noise can propagate into analog circuitry through the power pins of the circuit as a whole and op amp itself. Bypass capacitors are used to reduce the coupled noise by providing low-impedance power sources local to the analog circuitry.
  - Connect low-ESR, 0.1- $\mu\text{F}$  ceramic bypass capacitors between each supply pin and ground, placed as close to the device as possible. A single bypass capacitor from V+ to ground is applicable for single-supply applications.
- Separate grounding for analog and digital portions of circuitry is one of the simplest and most-effective methods of noise suppression. One or more layers on multilayer PCBs are usually devoted to ground planes. A ground plane helps distribute heat and reduces EMI noise pickup. Make sure to physically separate digital and analog grounds paying attention to the flow of the ground current. See [Circuit Board Layout Techniques](#), [SLOA089](#), for detailed information.
- In order to reduce parasitic coupling, run the input traces as far away from the supply or output traces as possible. If it is not possible to keep them separate, it is much better to cross the sensitive trace perpendicular as opposed to in parallel with the noisy trace.
- Place the external components as close to the device as possible. As shown in [Figure 44](#), keeping RF and RG close to the inverting input minimizes parasitic capacitance.
- Keep the length of input traces as short as possible. Always remember that the input traces are the most sensitive part of the circuit.
- Consider a driven, low-impedance guard ring around the critical traces. A guard ring can significantly reduce leakage currents from nearby traces that are at different potentials.

## 10.2 Layout Example

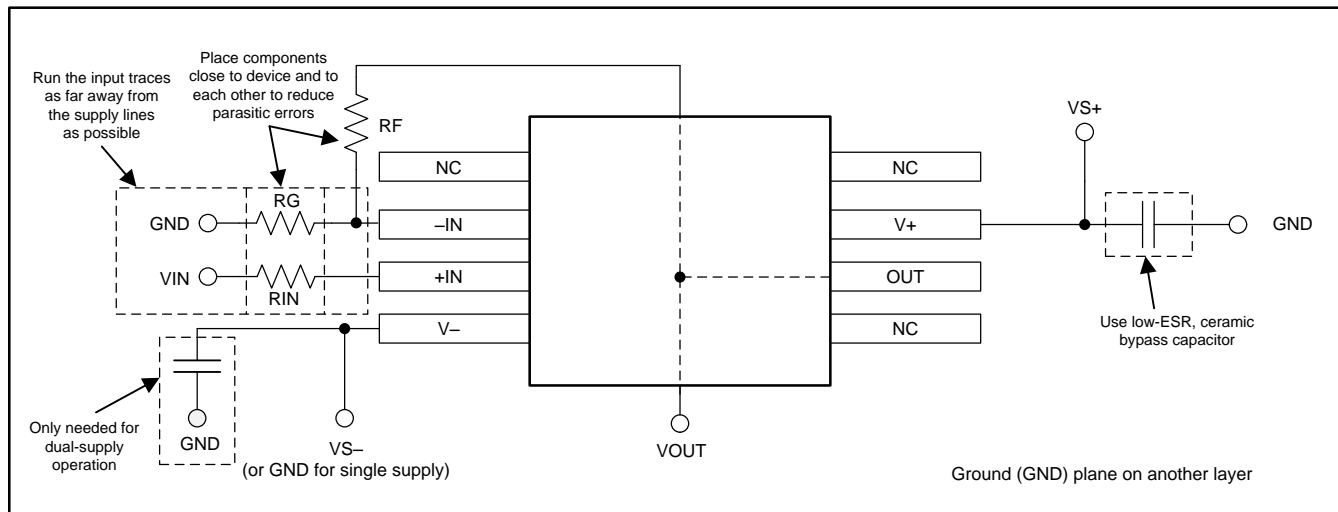
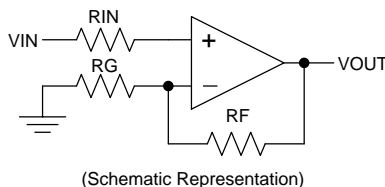


Figure 44. Operational Amplifier Board Layout for Noninverting Configuration

## 11 Device and Documentation Support

### 11.1 Documentation Support

#### 11.1.1 Related Documentation

For related documentation see the following:

- *Applications Bulletin AB-028, SBOA015*
- *Capacitive Load Drive Solution using an Isolation Resistor, TIDU032*
- *Circuit Board Layout Techniques, SLOA089*

### 11.2 Related Links

The table below lists quick access links. Categories include technical documents, support and community resources, tools and software, and quick access to sample or buy.

Table 4. Related Links

PARTS	PRODUCT FOLDER	SAMPLE & BUY	TECHNICAL DOCUMENTS	TOOLS & SOFTWARE	SUPPORT & COMMUNITY
OPA171-Q1	<a href="#">Click here</a>	<a href="#">Click here</a>	<a href="#">Click here</a>	<a href="#">Click here</a>	<a href="#">Click here</a>
OPA2171-Q1	<a href="#">Click here</a>	<a href="#">Click here</a>	<a href="#">Click here</a>	<a href="#">Click here</a>	<a href="#">Click here</a>
OPA4171-Q1	<a href="#">Click here</a>	<a href="#">Click here</a>	<a href="#">Click here</a>	<a href="#">Click here</a>	<a href="#">Click here</a>

### 11.3 Trademarks

All trademarks are the property of their respective owners.

## 11.4 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

## 11.5 Glossary

[SLYZ022](#) — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

## 12 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

**PACKAGING INFORMATION**

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
OPA171AQDBVRQ1	ACTIVE	SOT-23	DBV	5	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 125	OULQ	<a href="#">Samples</a>
OPA2171AQDRQ1	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-3-260C-168 HR	-40 to 125	2171AQ	<a href="#">Samples</a>
OPA4171AQDRQ1	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-3-260C-168 HR	-40 to 125	OPA4171Q1	<a href="#">Samples</a>
OPA4171AQPWRQ1	ACTIVE	TSSOP	PW	14	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-3-260C-168 HR	-40 to 125	O4171Q1	<a href="#">Samples</a>

(1) The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

**LIFEBUY:** TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBSELETE:** TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check <http://www.ti.com/productcontent> for the latest availability information and additional product content details.

**TBD:** The Pb-Free/Green conversion plan has not been defined.

**Pb-Free (RoHS):** TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

**Pb-Free (RoHS Exempt):** This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

**Green (RoHS & no Sb/Br):** TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

**Important Information and Disclaimer:**The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

**OTHER QUALIFIED VERSIONS OF OPA171-Q1, OPA2171-Q1, OPA4171-Q1 :**

- Catalog: [OPA171](#), [OPA2171](#), [OPA4171](#)

NOTE: Qualified Version Definitions:

- Catalog - TI's standard catalog product

**TAPE AND REEL INFORMATION**

**QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE**


\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
OPA171AQDBVRQ1	SOT-23	DBV	5	3000	180.0	8.4	3.23	3.17	1.37	4.0	8.0	Q3
OPA2171AQDRQ1	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
OPA4171AQDRQ1	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
OPA4171AQPWRQ1	TSSOP	PW	14	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1

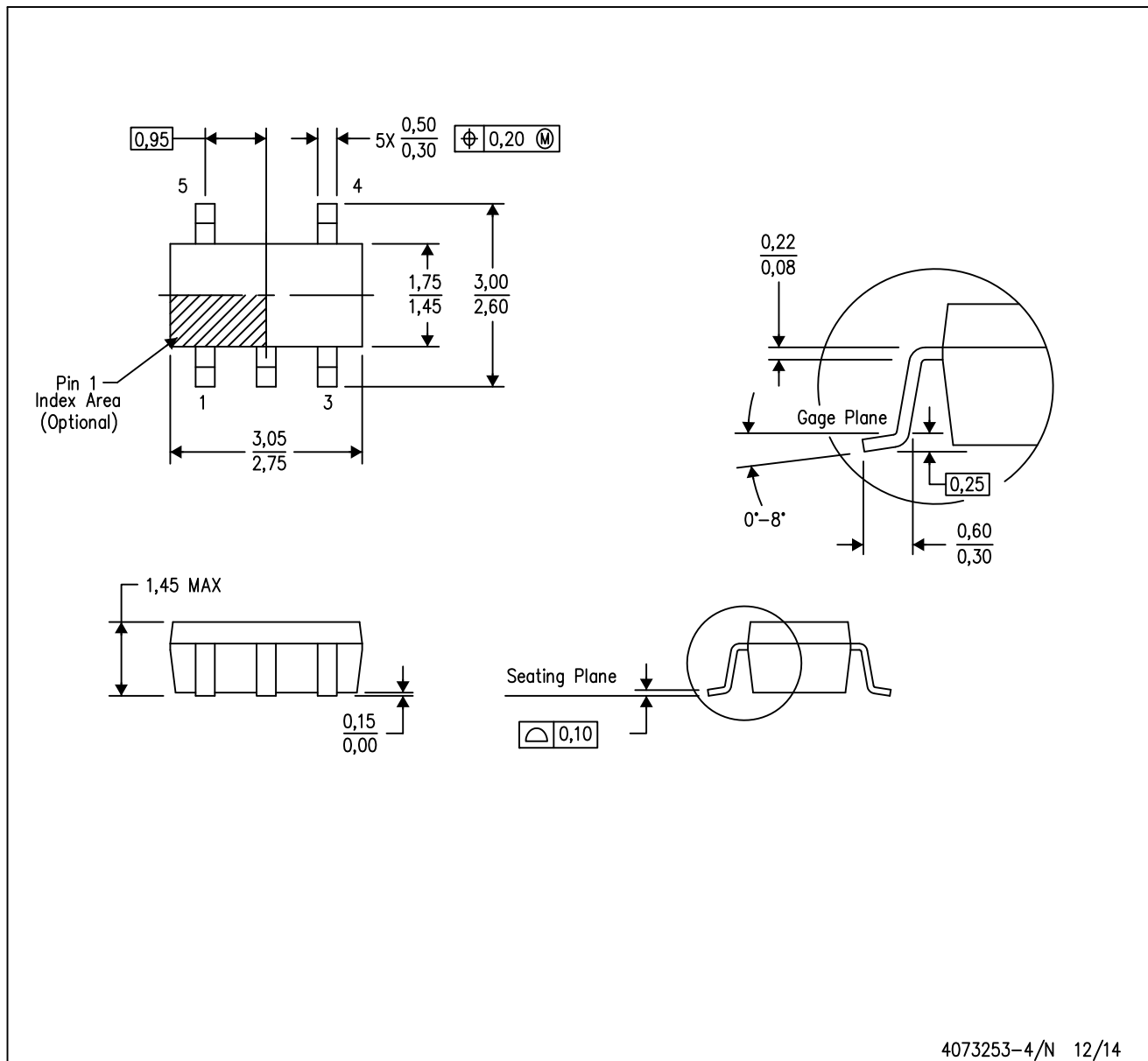
**TAPE AND REEL BOX DIMENSIONS**


\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
OPA171AQDBVRQ1	SOT-23	DBV	5	3000	202.0	201.0	28.0
OPA2171AQDRQ1	SOIC	D	8	2500	533.4	186.0	36.0
OPA4171AQDRQ1	SOIC	D	14	2500	367.0	367.0	38.0
OPA4171AQPWRQ1	TSSOP	PW	14	2000	367.0	367.0	35.0

DBV (R-PDSO-G5)

PLASTIC SMALL-OUTLINE PACKAGE



- NOTES:
- A. All linear dimensions are in millimeters.
  - B. This drawing is subject to change without notice.
  - C. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
  - D. Falls within JEDEC MO-178 Variation AA.

D (R-PDSO-G14)

PLASTIC SMALL OUTLINE



- NOTES:
- A. All linear dimensions are in inches (millimeters).
  - B. This drawing is subject to change without notice.
  - $\triangle C$  Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
  - $\triangle D$  Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
  - E. Reference JEDEC MS-012 variation AB.

D (R-PDSO-G14)

PLASTIC SMALL OUTLINE



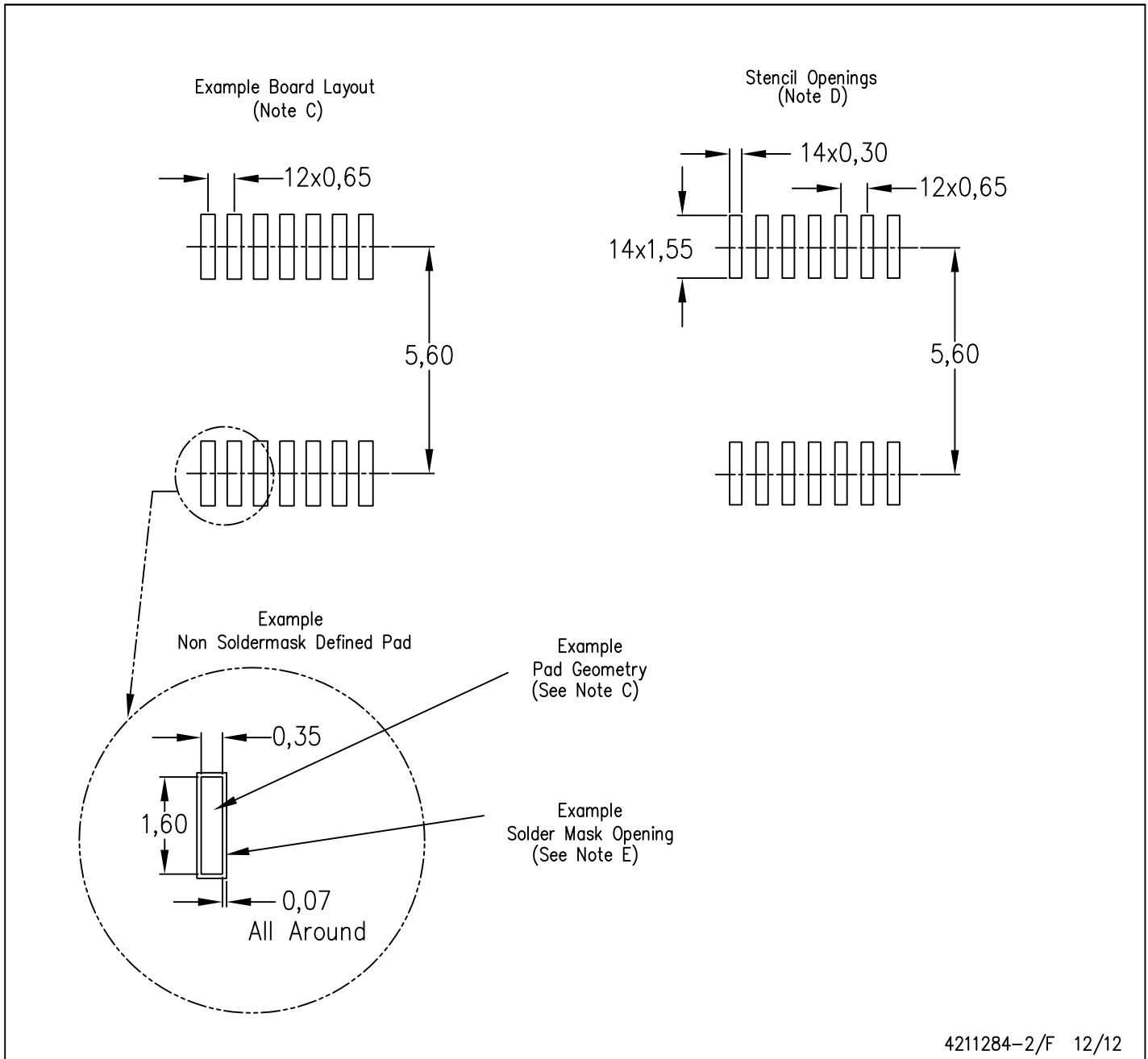
4211283-3/E 08/12

- NOTES:
- A. All linear dimensions are in millimeters.
  - B. This drawing is subject to change without notice.
  - C. Publication IPC-7351 is recommended for alternate designs.
  - D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
  - E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



PW (R-PDSO-G14)

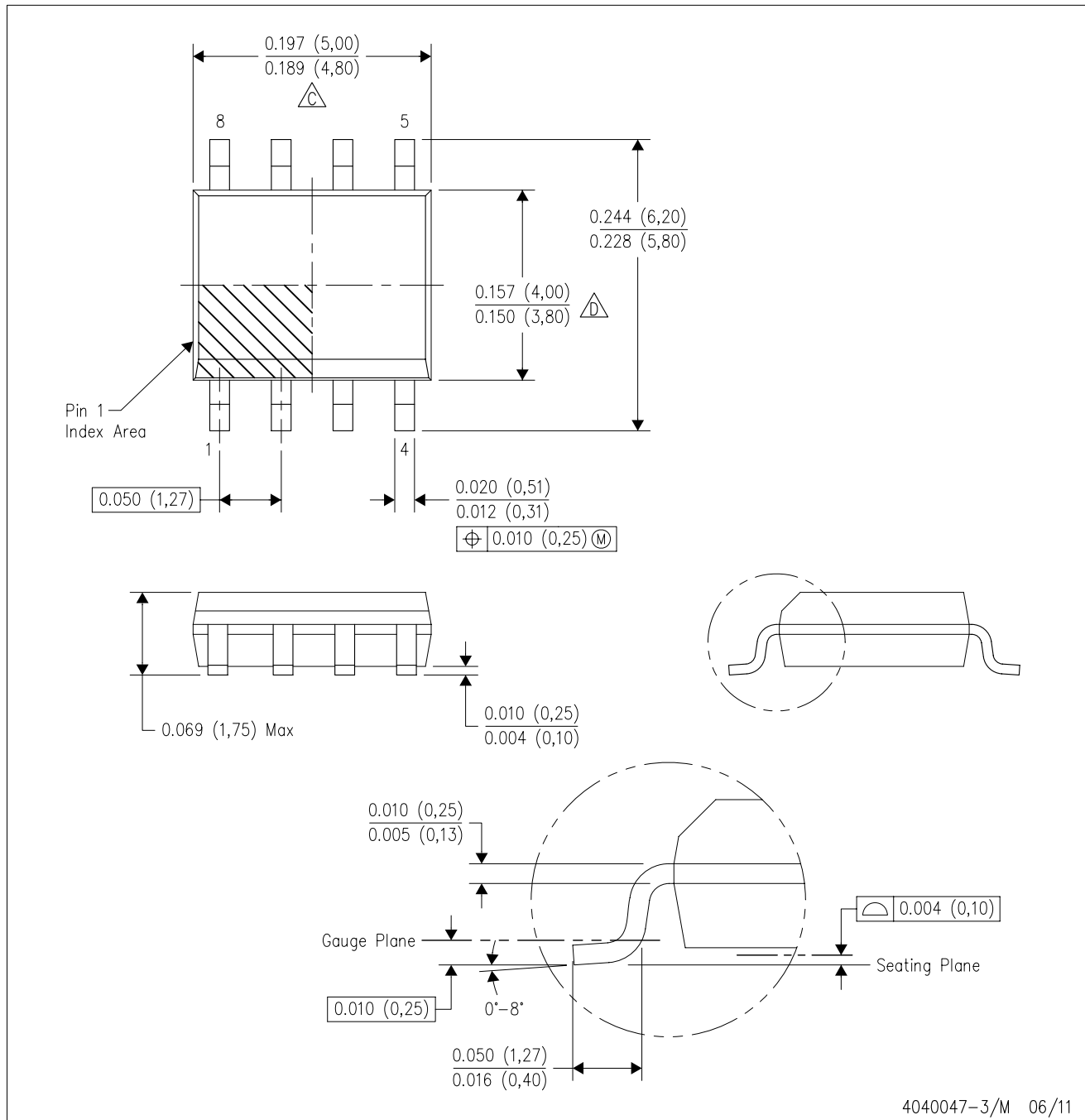
PLASTIC SMALL OUTLINE



- NOTES:
- All linear dimensions are in millimeters.
  - This drawing is subject to change without notice.
  - Publication IPC-7351 is recommended for alternate designs.
  - Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
  - Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

D (R-PDSO-G8)

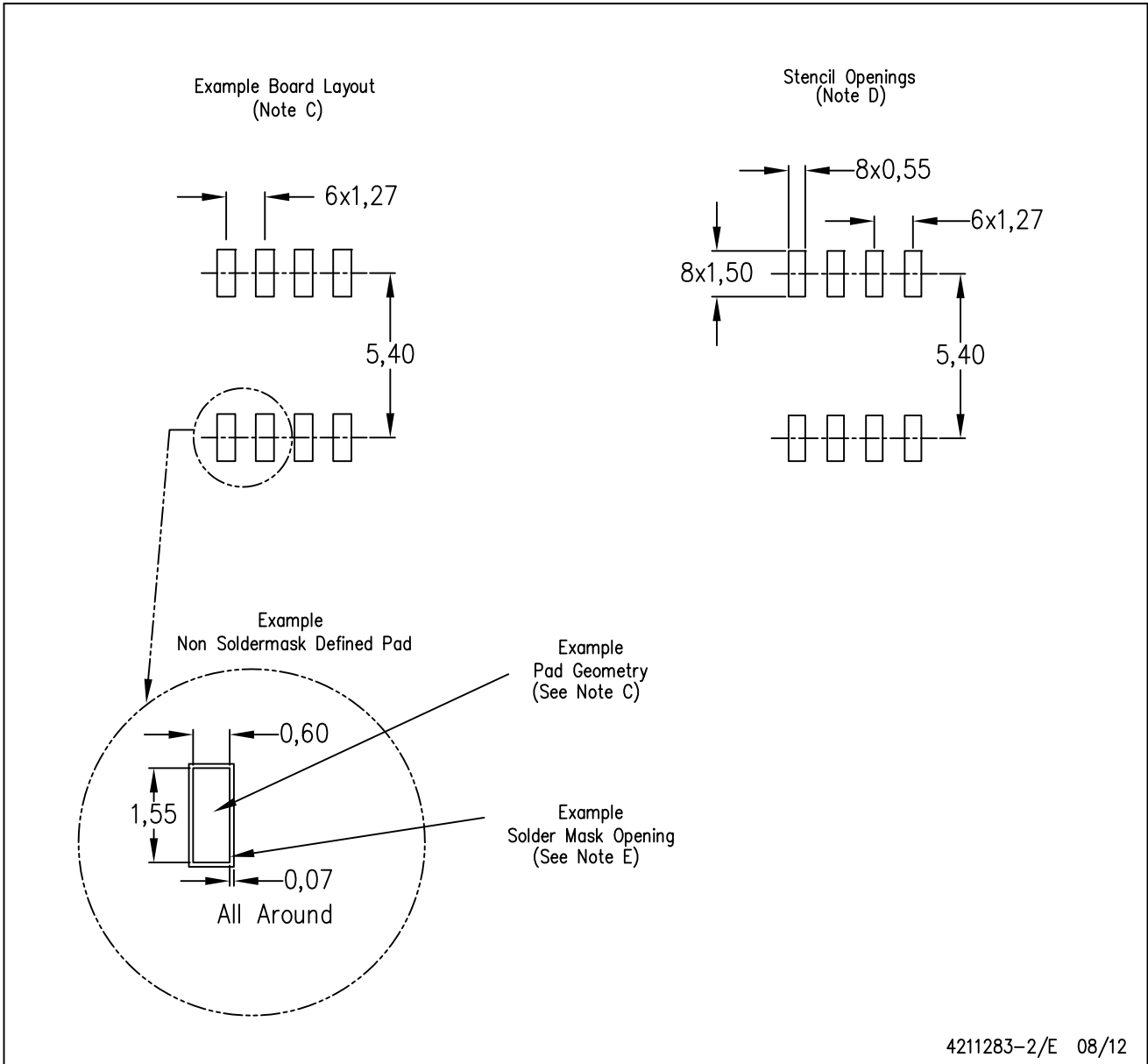
PLASTIC SMALL OUTLINE



- NOTES:
- A. All linear dimensions are in inches (millimeters).
  - B. This drawing is subject to change without notice.
  - Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
  - Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
  - E. Reference JEDEC MS-012 variation AA.

D (R-PDSO-G8)

PLASTIC SMALL OUTLINE



- NOTES:
- A. All linear dimensions are in millimeters.
  - B. This drawing is subject to change without notice.
  - C. Publication IPC-7351 is recommended for alternate designs.
  - D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
  - E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

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